

REMARKS


Applicants have amended the claims of the above-identified application by adding new claim 2 and 3 to the application. New claim 2, dependent on claim 1, further defines the first and second mask patterns, respectively as a pattern for transferring a gate pattern and as a pattern for removing an unnecessary portion transferred on the positive type photoresist film at the time of transfer using the first mask pattern. Claim 3, dependent on claim 2, recites that the gate pattern is a gate pattern in an SRAM memory cell. Note, for example, the third full paragraph on page 73 of Applicants' specification. Note also the paragraph bridging pages 5 and 6, as well as the description on pages 45-68, of Applicants' specification.

Entry of the present amendments, and of the amendments in the Preliminary Amendment filed July 22, 2003, and, subsequent thereto, examination of the above-identified application in due course, are respectfully requested.

To the extent necessary, Applicants petition for an extension of time under 37 CFR 1.136. Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to the Deposit Account No. 01-2135 (Case No. 843.40352CX1), and please credit any excess fees to such Deposit Account.

Respectfully submitted,

ANTONELLI, TERRY, STOUT & KRAUS, LLP

By 
William I. Solomon
Reg. No. 28,565

WIS/dlt

FAKX RECEIVED
AUG 25 2003
TC 1700

1300 North Seventeenth Street, Suite 1800
Arlington, Virginia 22209
Telephone: (703) 312-6600
Facsimile: (703) 312-6666

OFFICIAL